

# Band switching diode

## 1SS390 **New**

### ● Applications

High frequency switching

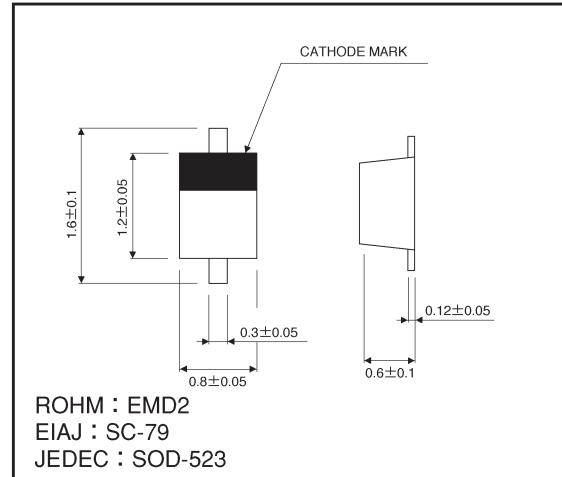
### ● Features

- 1) Extremely small surface mounting type. (EMD2)
- 2) High reliability.

### ● Construction

Silicon epitaxial planar

### ● External dimensions (Units: mm)



### ● Absolute maximum ratings ( $T_a = 25^\circ\text{C}$ )

Parameter	Symbol	Limits	Unit
DC reverse voltage	$V_R$	35	V
DC forward current	$I_F$	100	mA
Junction temperature	$T_j$	125	°C
Storage temperature	$T_{stg}$	-55~+125	°C

### ● Electrical characteristics ( $T_a = 25^\circ\text{C}$ )

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Forward voltage	$V_F$	—	0.83	1.0	V	$I_F=10\text{mA}$
Reverse current	$I_R$	—	0.01	10	nA	$V_R=25\text{V}$
Capacitance between terminals	$C_T$	—	0.80	1.2	pF	$V_R=6\text{V}, f=1\text{MHz}$
Forward operating resistance	$r_F$	—	0.62	0.9	Ω	$I_F=2\text{mA}, f=100\text{MHz}$

● Electrical characteristic curves ( $T_a = 25^\circ\text{C}$  unless specified otherwise)

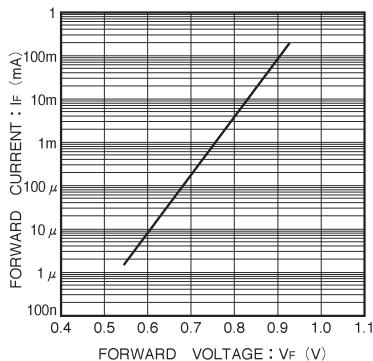


Fig. 1 Forward characteristics

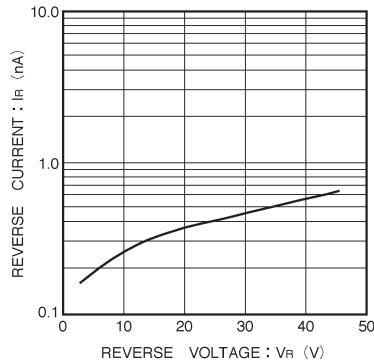


Fig. 2 Reverse characteristics

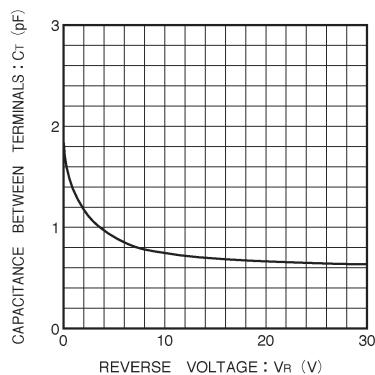


Fig. 3 Capacitance between terminals characteristics

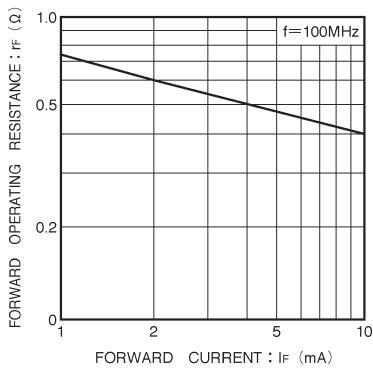


Fig. 4 Forward operating resistance characteristics

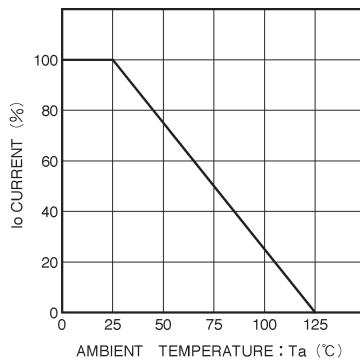


Fig. 5 Derating curve  
(mounting on glass epoxy PCBs)